# P-Channel 30-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

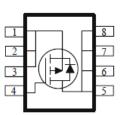
<b>Typical</b>	Applications	
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
-30	5 @ VGS = -10V	-21	
	7 @ VGS = -4.5V	-17	







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage		$V_{DS}$	-30	V	
Gate-Source Voltage			±20	V	
Continuous Drain Current a	T <sub>A</sub> =25°C	· I <sub>D</sub>	-21		
Continuous Drain Current	T <sub>A</sub> =70°C	'D	-17	Α	
Pulsed Drain Current <sup>b</sup>			-80		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-4.8	Α		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	3.1	W	
Fower Dissipation	T <sub>A</sub> =70°C	' D	2.2	V V	
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Ambient	Steady State	IN <sub>θ</sub> JΑ	80		

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

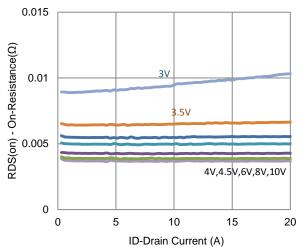
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	1			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	-1 uA
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-30			Α
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_D = -10.5 \text{ A}$			5	mΩ
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -8.5 \text{ A}$			7	11122
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -10.5 \text{ A}$		32		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -2.4 \text{ A}, V_{GS} = 0 \text{ V}$		-0.68		V
		Dynamic <sup>b</sup>				
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		136		
Gate-Source Charge	$Q_{gs}$	$I_{DS} = -13 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -10.5 \text{ A}$		31		nC
Gate-Drain Charge	$Q_gd$	10 = 10.5 A		59		
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -15 \text{ V}, R_1 = 1.9 \Omega,$		19		
Rise Time	t <sub>r</sub>	$V_{DS} = -13 \text{ V}, K_L = 1.9 \Omega,$ $I_D = -10.5 \text{ A},$		64		ne
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		365		ns
Fall Time	$t_f$	V GEN - 10 V, T GEN - 0 12		224		
Input Capacitance	C <sub>iss</sub>			9350		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1415		pF
Reverse Transfer Capacitance	$C_{rss}$			1034		

#### Notes

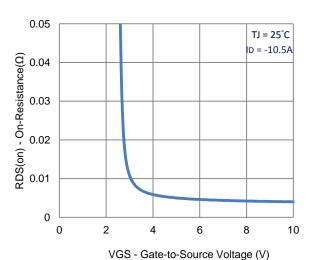
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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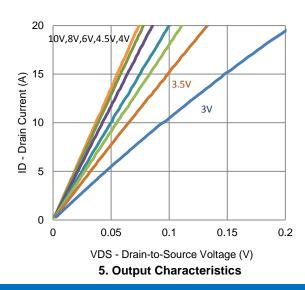
## **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



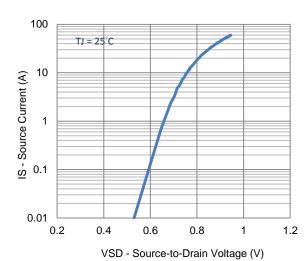
20
TJ = 25°C

(Y) tuesto 10

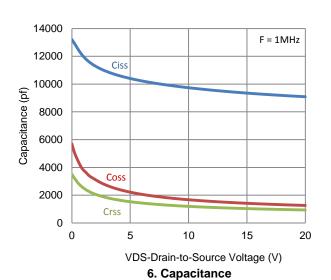
10
0 1 2 3 4

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

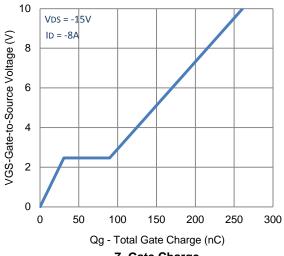


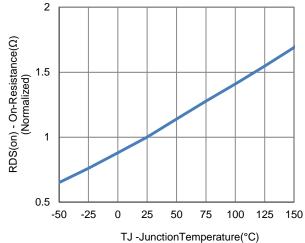
4. Drain-to-Source Forward Voltage



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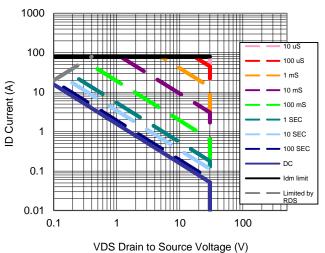
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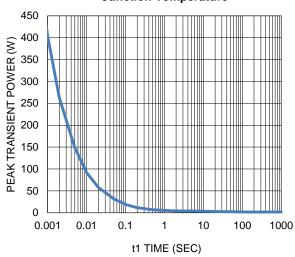




7. Gate Charge

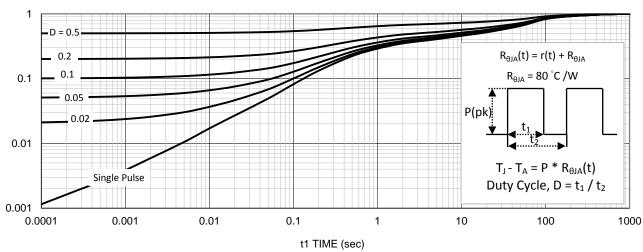






9. Safe Operating Area

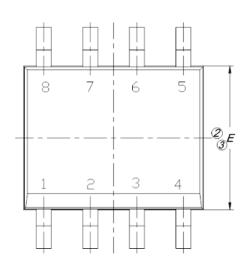
10. Single Pulse Maximum Power Dissipation

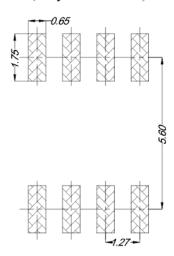


11. Normalized Thermal Transient Junction to Ambient

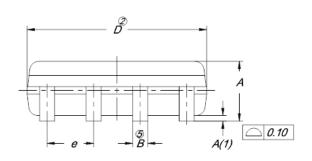
### **Package Information**

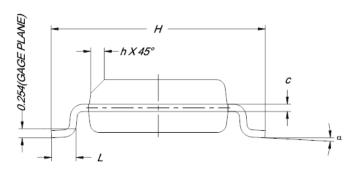
Land Pattern (Only for Reference)





5114	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
Α	1.35	1.55	1.75	
A(1)	0.10	0.18	0.25	
В	0.38	0.45	0.51	
С	0.19	0.22	0.25	
D	4.80	4.90	5.00	
E	3.80	3.90	4.00	
е	1.27 BSC			
Н	5.80	6.00	6.20	
L	0.50	0.72	0.93	
α	0°	4°	8°	
h	0.25	0.38	0.50	





#### Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.